PTO/SB/08A (10-01)
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known	
Application Number	09/988,627
Filing Date	November 20, 2001
First Named Inventor	Glen Hush
Art Unit	2824
Examiner Name	N. Nguyen
Attorney Docket Number	M4065.0478/P478

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
NTN	AA	2000/0072188 App	6/2002	Gilton	
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Sheet 2 of 3

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Art Unit	2824
Examiner Name	N. Nguyen
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Examiner Signature	Nam Nguyen	Date Considered	2/10/2004

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 3 of 3

Complete if Known	
Application Number	09/988,627
Filing Date	November 20, 2001
First Named Inventor	Glen Hush
Group Art Unit	2824
Examiner Name	N. Nguyen
Attorney Docket Number	M4065.0483/P483

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Examiner Signature	Nam Nguyen	Date Considered	2/10/04

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